

Chapter 7: Diffusion

❑ ISSUES TO ADDRESS

- ❖ How does diffusion occur?
- ❖ Why is it an important part of processing?
- ❖ How can the rate of diffusion be predicted for some simple cases?
- ❖ How does diffusion depend on structure and temperature?



- Case Hardening:
 - Diffuse carbon atoms into the host iron atoms at the surface.
 - Example of interstitial diffusion is a case hardened gear.
- Result: The presence of C atoms makes iron (steel) harder.



7.1 Introduction to Diffusion

❑ Diffusion: Material transport by atomic motion

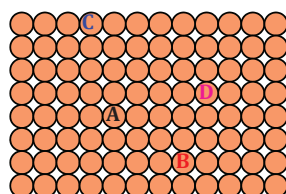
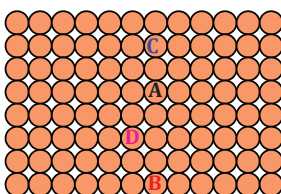
❑ Mechanisms

- ❖ Gases & Liquids – random (Brownian) motion
- ❖ Solids – vacancy diffusion or interstitial diffusion

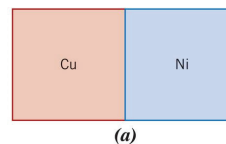
❑ Self-diffusion: In an elemental solid, atoms also migrate.

Label some atoms

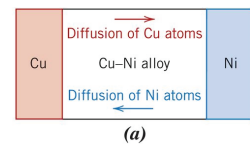
After some time



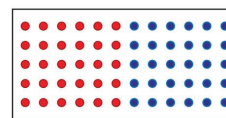
❑ Interdiffusion: In an alloy, atoms tend to migrate from regions of high concentration to regions of low concentration.



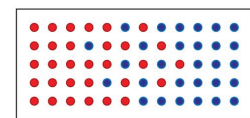
(a)



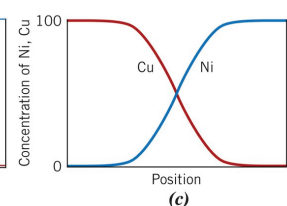
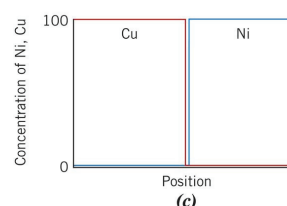
(a)



(b)



(b)



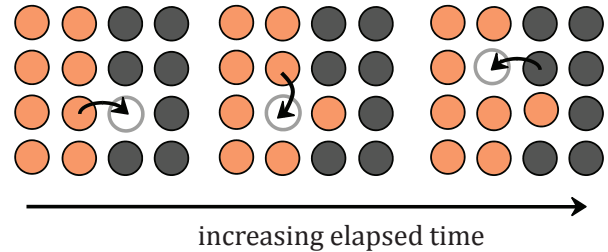
Figs. 7.1 & 7.2, Callister & Rethwisch 9e.

7.2 Diffusion Mechanisms

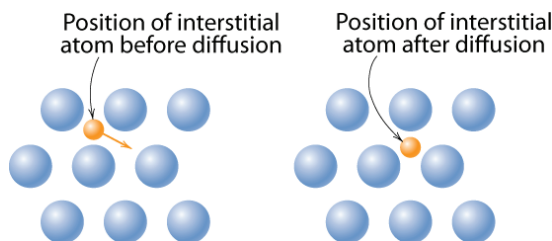
- ❑ **Diffusion: Stepwise migration of atoms from lattice site to lattice site. For this,**
 - (1) there must be an empty adjacent site, and
 - (2) the atom must have sufficient energy to break bonds with its neighbor atoms.

- ❑ **Vacancy Diffusion:**

- ❖ atoms exchange with vacancies
- ❖ applies to substitutional impurities atoms
- ❖ rate depends on:
 - number of vacancies
 - activation energy to exchange.



- ❑ **Interstitial diffusion: smaller atoms can diffuse between atoms.**



- Ex: hydrogen, carbon, nitrogen, oxygen, etc.
- More rapid than vacancy diffusion

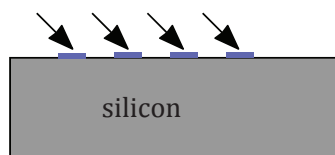
Fig. 7.3 (b), Callister & Rethwisch 9e.

Processing Using Diffusion

- ❑ **Doping silicon with phosphorus for n-type semiconductors:**

- ❑ **Process:**

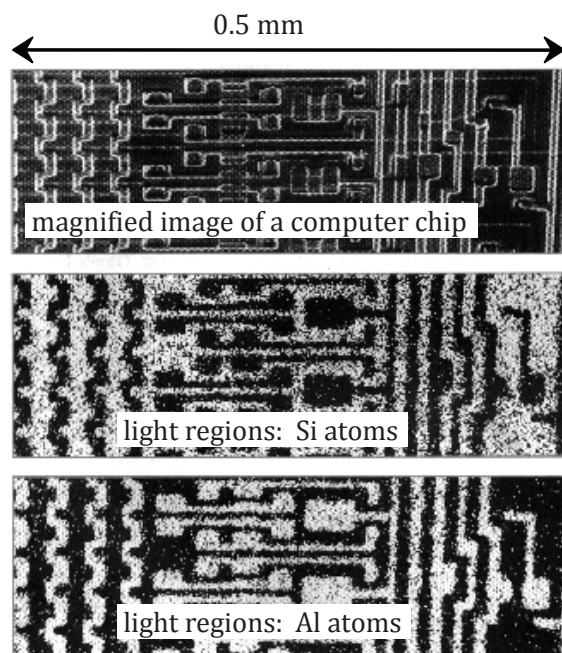
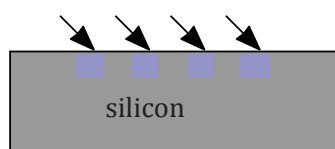
1. Deposit P rich layers on surface.



2. Heat it.



3. Result: Doped semiconductor regions.



Adapted from Figure 19.27, Callister & Rethwisch 9e.

7.3 Steady-State Diffusion

- How do we quantify the amount or rate of diffusion?

$$J \equiv \text{Diffusion flux} \equiv \frac{\text{moles (or mass) diffusing}}{(\text{area})(\text{time})} = \frac{\text{mol}}{\text{cm}^2\text{s}} \text{ or } \frac{\text{kg}}{\text{m}^2\text{s}}$$

- Measured empirically

- ❖ Make thin film (membrane) of known cross-sectional area
- ❖ Impose concentration gradient
- ❖ Measure how fast atoms or molecules diffuse through the membrane

$$J = \frac{M}{At} = \frac{l}{A} \frac{dM}{dt}$$

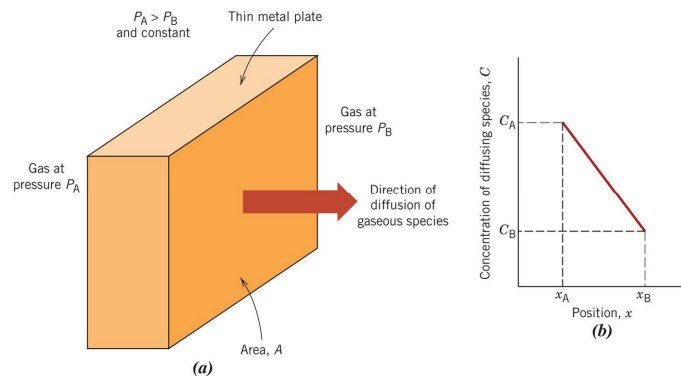
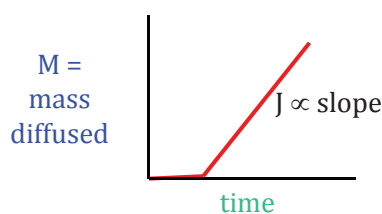
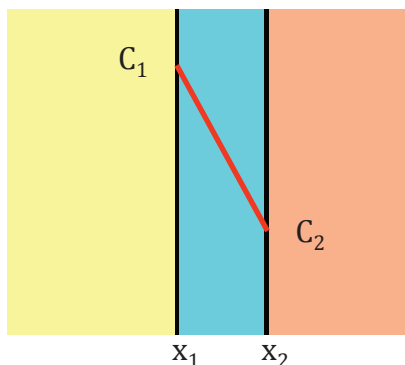


Fig. 7.4, Callister & Rethwisch 9e.

7.3 Steady-State Diffusion

- Rate of diffusion is independent of time
- Flux is proportional to concentration gradient = $\frac{dC}{dx}$



Fick's first law of diffusion

$$J = -D \frac{dC}{dx}$$

D ≡ diffusion coefficient [m²/s]

if linear $\frac{dC}{dx} \cong \frac{\Delta C}{\Delta x} = \frac{C_2 - C_1}{x_2 - x_1}$

- Concentration gradient is the driving force of diffusion

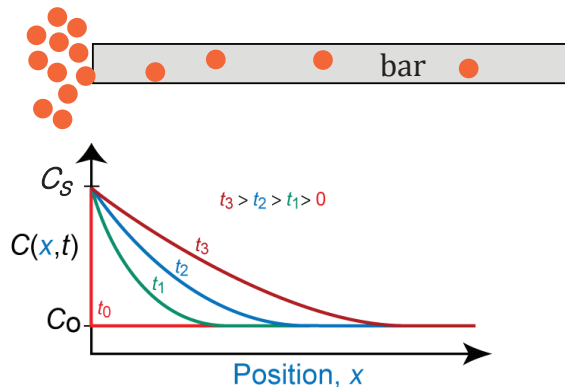
7.4 Nonsteady-State Diffusion

- ❑ The concentration of diffusing species is a function of both time and position, that is, $C = C(x, t)$.

- ❑ Fick's Second Law:
$$\frac{\partial C}{\partial t} = \frac{\partial}{\partial x} \left(D \frac{\partial C}{\partial x} \right) \quad \text{or} \quad \frac{\partial C}{\partial t} = D \frac{\partial^2 C}{\partial x^2} \quad \text{for constant } D$$

- ❑ Example: Copper diffuses into a bar of aluminum.

- ❖ C_0 = pre-existing concentration of Cu atoms
- ❖ C_s = Surface concentration, of Cu atoms



Boundary Conditions

at $t = 0$, $C = C_0$ for $0 \leq x \leq \infty$

at $t > 0$, $C = C_s$ (constant) for $x = 0$

$C = C_0$ for $x = \infty$

Fig. 7.5, Callister & Rethwisch 9e.

7.4 Nonsteady-State Diffusion

$$\therefore \frac{C(x, t) - C_0}{C_s - C_0} = 1 - \operatorname{erf} \left(\frac{x}{2\sqrt{Dt}} \right)$$

- ❖ $C(x, t)$ = Conc. at point x at time t
- ❖ $\operatorname{erf}(z)$ = Gaussian error function
- ❖ $\operatorname{erf}(z) = \frac{2}{\sqrt{\pi}} \int_0^z e^{-y^2} dy$
- ❖ $\operatorname{erf}(z)$ values are given in Table 7.1

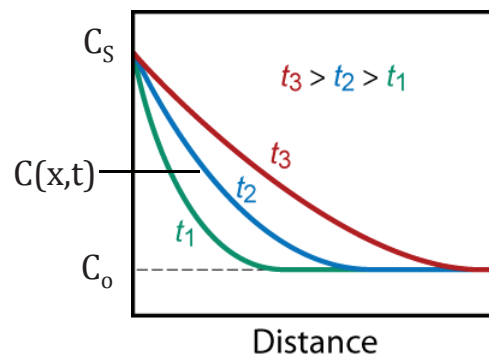


Fig. 7.5, Callister & Rethwisch 9e.

- ❑ Sample Problem

- ❖ An FCC iron-carbon alloy initially containing 0.20 wt% C is carburized at an elevated temperature and in an atmosphere that gives a surface carbon concentration constant at 1.0 wt%. If after 49.5 h the concentration of carbon is 0.35 wt% at a position 4.0 mm below the surface, determine the temperature at which the treatment was carried out.
- ❖ Hint: Use Eq. 7.5

7.5 Factors That Influence Diffusion

- Temperature has a profound influence on the coefficients and diffusion rates.

$$\therefore D = D_0 \exp\left(-\frac{Q_d}{RT}\right)$$

- ❖ Diffusion coefficient increases with increasing T.
- ❖ D_0 = a temperature-independent preexponential (m^2/s)
- ❖ Q_d = the activation energy for diffusion (J/mol or eV/atom)
- ❖ R = the gas constant, 8.314 J/mol-K or $8.62 \times 10^{-5} \text{ eV/atom-K}$
- ❖ T = absolute temperature (K)

- D has exponential dependence on T .

- $D_{\text{interstitial}} \gg D_{\text{substitutional}}$

- ❖ Ex. of interstitial diffusion: C in α -Fe, C in γ -Fe, etc.
- ❖ Ex. of substitutional diffusion: Al in Al, Fe in α -Fe, Fe in γ -Fe, etc.

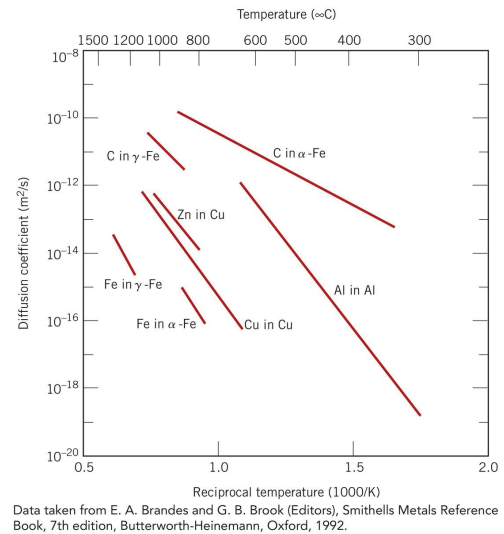


Fig. 7.7, Callister & Rethwisch 9e

Summary of Diffusion

- Solid-state diffusion is a means of mass transport within solid materials by stepwise atomic motion.

- Two diffusion mechanisms:

- ❖ Vacancy diffusion
- ❖ Interstitial diffusion

- Fick's second law (diffusion equation): $\frac{\partial C}{\partial t} = D \left(\frac{\partial^2 C}{\partial x_1^2} + \frac{\partial^2 C}{\partial x_2^2} + \frac{\partial^2 C}{\partial x_3^2} \right)$

- Temperature has a profound influence on the coefficients and diffusion rates.

$$\therefore D = D_0 \exp\left(-\frac{Q_d}{RT}\right)$$

- Diffusion **FASTER** for...

- open crystal structures
- materials with secondary bonding
- smaller diffusing atoms
- lower density materials

- Diffusion **SLOWER** for...

- close-packed structures
- materials with covalent bonding
- larger diffusing atoms
- higher density materials